

Features

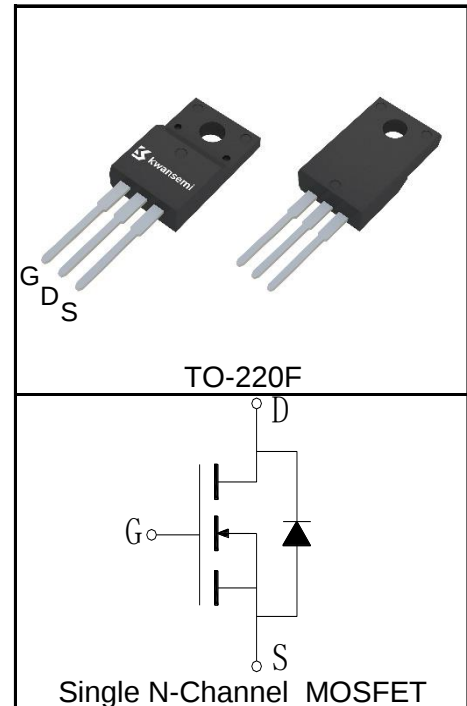
- 200V/14A,
 $R_{DS(ON)} = 145m\Omega(Typ.)@V_{GS}=10V$
- Low $R_{DS(ON)}$
- Planar Technology
- Reliable and Rugged
- 100% Avalanche Tested
- 100% Rg Tested

Applications

- Inverter
- Motor Control



Pin Description



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_C=25^\circ\text{C}$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	200	V
V_{GSS}	Gate-Source Voltage	± 30	
T_J	Maximum Junction Temperature	175	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ\text{C}$
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ 14	A
Mounted on Large Heat Sink			
$I_{DP}^{①}$	300 μs Pulse Drain Current Tested	$T_C=25^\circ\text{C}$ 56	A
$I_D^{②}$	Continuous Drain Current($V_{GS}=10V$)	$T_C=25^\circ\text{C}$ 14	A
		$T_C=100^\circ\text{C}$ 10	
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 56	W
		$T_C=100^\circ\text{C}$ 28	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	2.7	$^\circ\text{C/W}$
$R_{\theta JA}^{③}$	Thermal Resistance-Junction to Ambient	62.5	$^\circ\text{C/W}$
Drain-Source Avalanche Ratings			
$E_{AS}^{④}$	Avalanche Energy, Single Pulsed	90	mJ

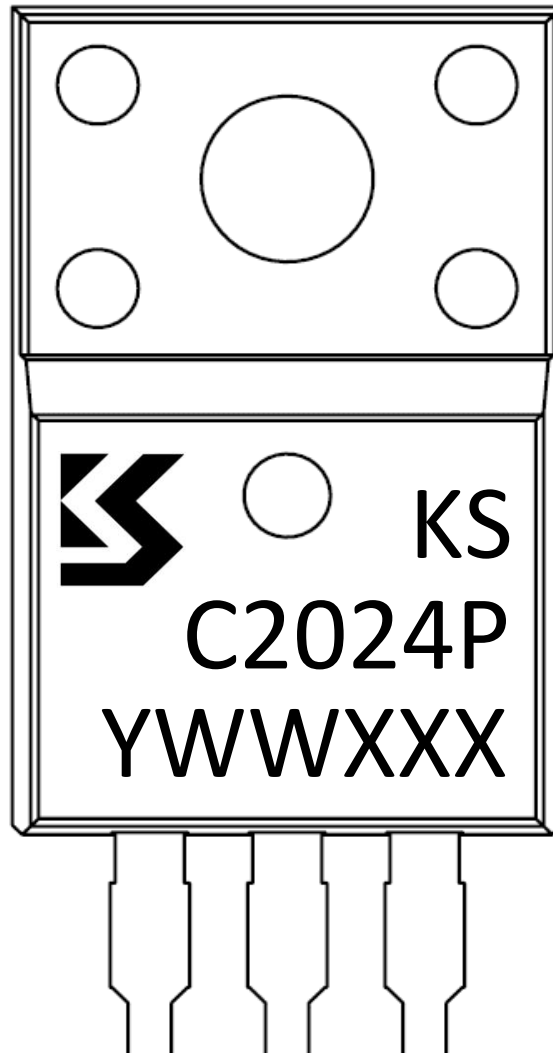
Electrical Characteristics ($T_C=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	KSC2024FAP			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	200			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =200V, V _{GS} =0V			1	μA
		T _J =125°C			30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	2	3	4	V
I _{GSS}	Gate Leakage Current	V _{GS} =±30V, V _{DS} =0V			±100	nA
R _{DS(ON)} ⑤	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =9A		145	180	mΩ
		V _{GS} =6V, I _{DS} =4A		160	210	mΩ
Diode Characteristics						
V _{SD} ⑤	Diode Forward Voltage	I _{SD} =9A, V _{GS} =0V		0.82	1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =9A, dI _{SD} /dt=100A/μs		55		ns
Q _{rr}	Reverse Recovery Charge			131		nC
Dynamic Characteristics ⑥						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	0.5	1.3	2	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =100V, Frequency=1.0MHz		2230		pF
C _{oss}	Output Capacitance			205		
C _{rss}	Reverse Transfer Capacitance			50		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =100V, I _{DS} =9A, V _{GEN} =10V, R _G =3Ω		14		ns
t _r	Turn-on Rise Time			48		
t _{d(OFF)}	Turn-off Delay Time			89		
t _f	Turn-off Fall Time			30		
Gate Charge Characteristics ⑥						
Q _g	Total Gate Charge	V _{DS} =100V, V _{GS} =10V, I _{DS} =9A		55		nC
Q _{gs}	Gate-Source Charge			17		
Q _{gd}	Gate-Drain Charge			16		

- Notes:
- ① Pulse width limited by safe operating area.
 - ② Calculated continuous current based on maximum allowable junction temperature.
 - ③ When mounted on 1 inch square copper board, $t \leq 10\text{sec}$. The value in any given application depends on the user's specific board design.
 - ④ Limited by T_{Jmax} , $I_{AS} = 19A$, $L=0.5\text{mH}$, $V_{DD} = 48V$, $R_G = 25\Omega$, Starting $T_J = 25^{\circ}\text{C}$, 100% tested and guaranteed.
 - ⑤ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - ⑥ Guaranteed by design, not subject to production testing.

Ordering and Marking Information

Device	Package	Packaging	Quantity	Reel Size	Tape width
KSC2024FAP	TO-220F	Tube	50	-	-

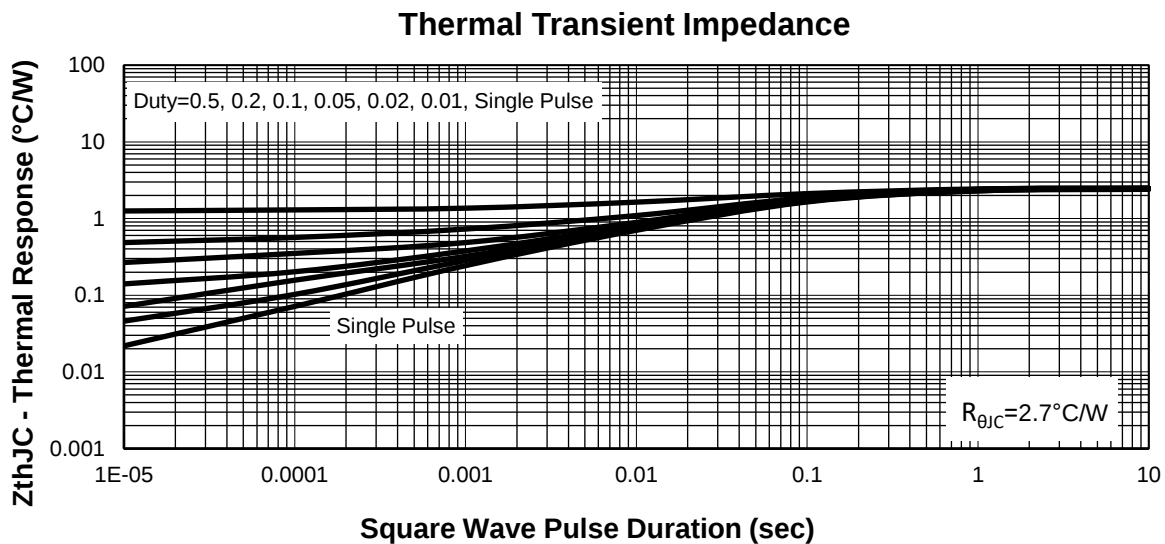
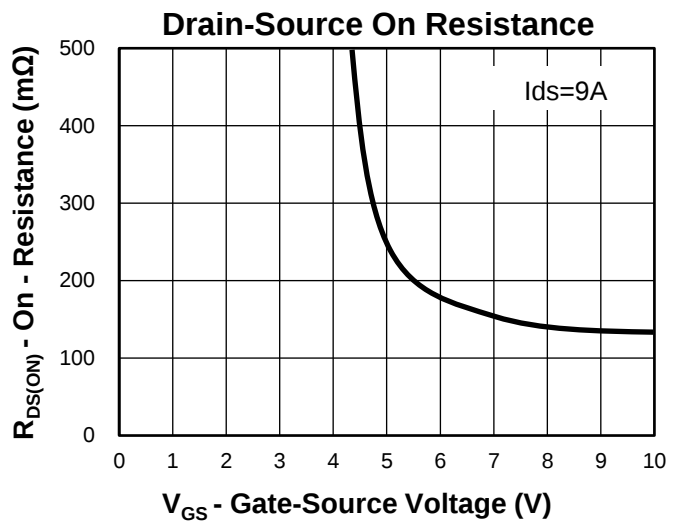
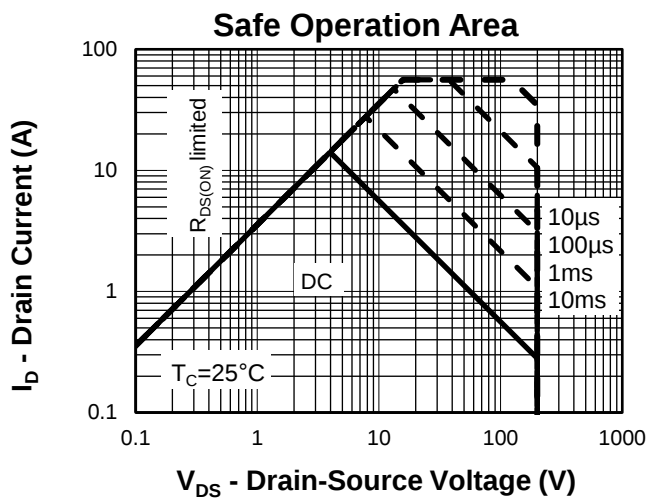
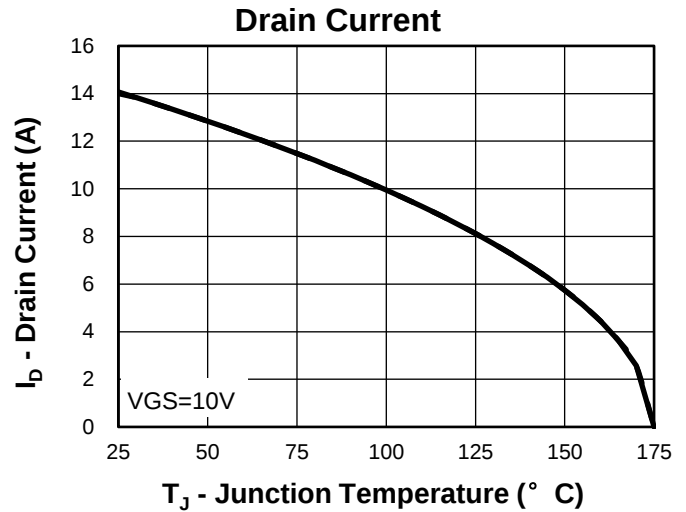
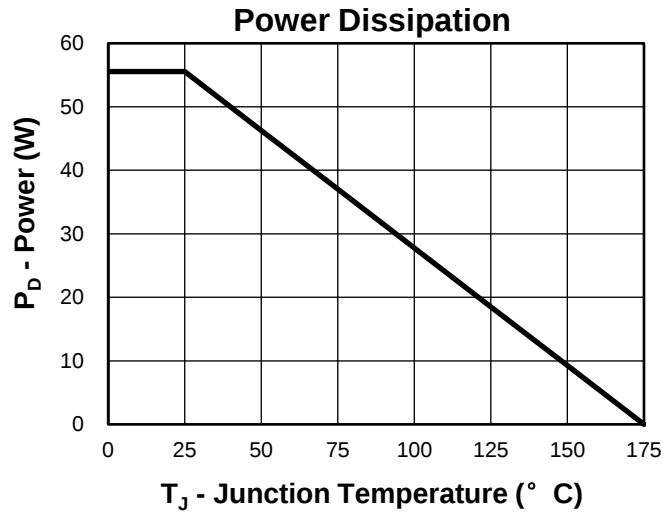


1st Line: Kwansemi LOGO, Kwansemi Code(KS)

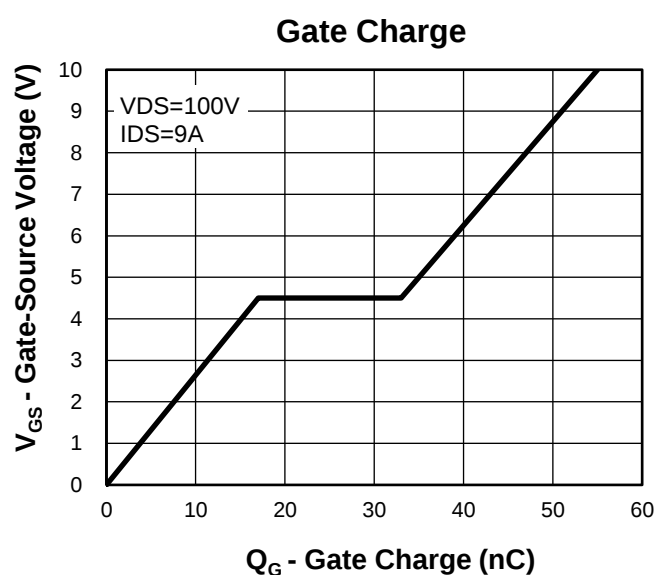
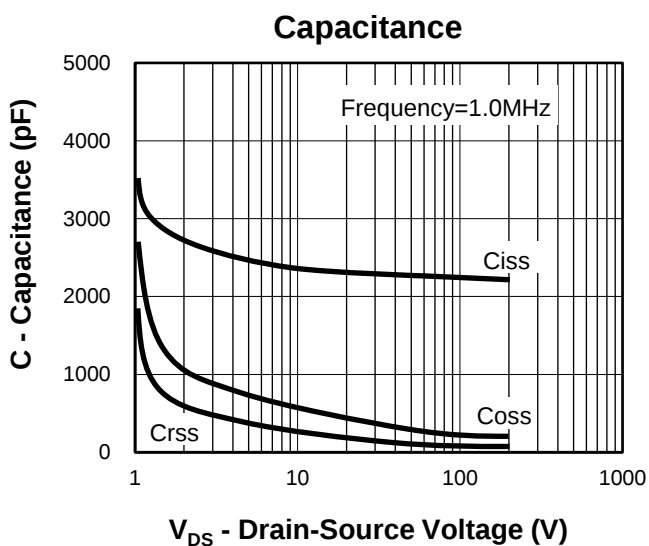
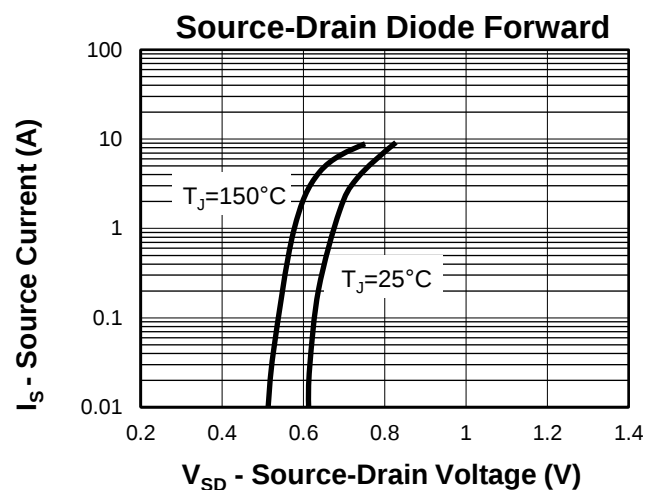
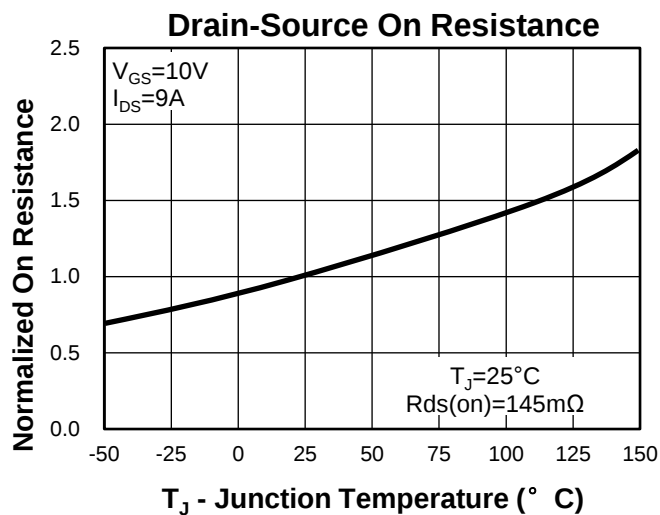
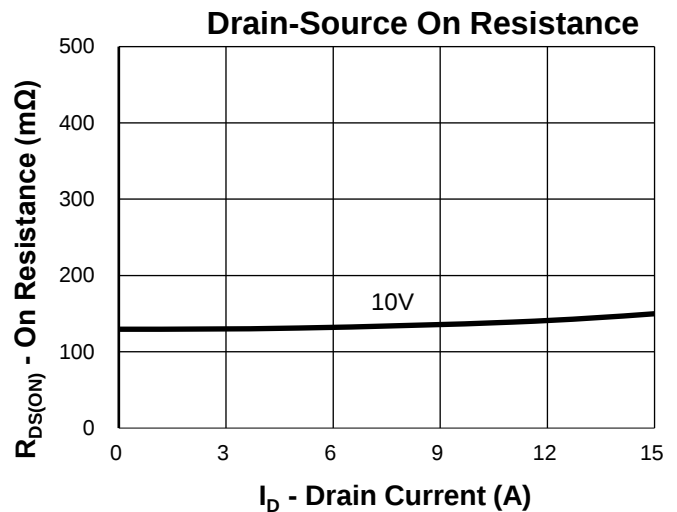
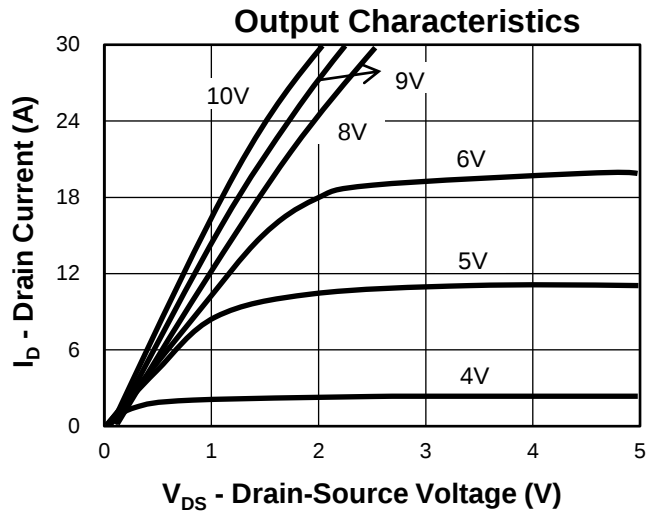
2nd Line: Part Number(C2024P)

3rd Line: Lot Number(YWWXXX)

Typical Characteristics

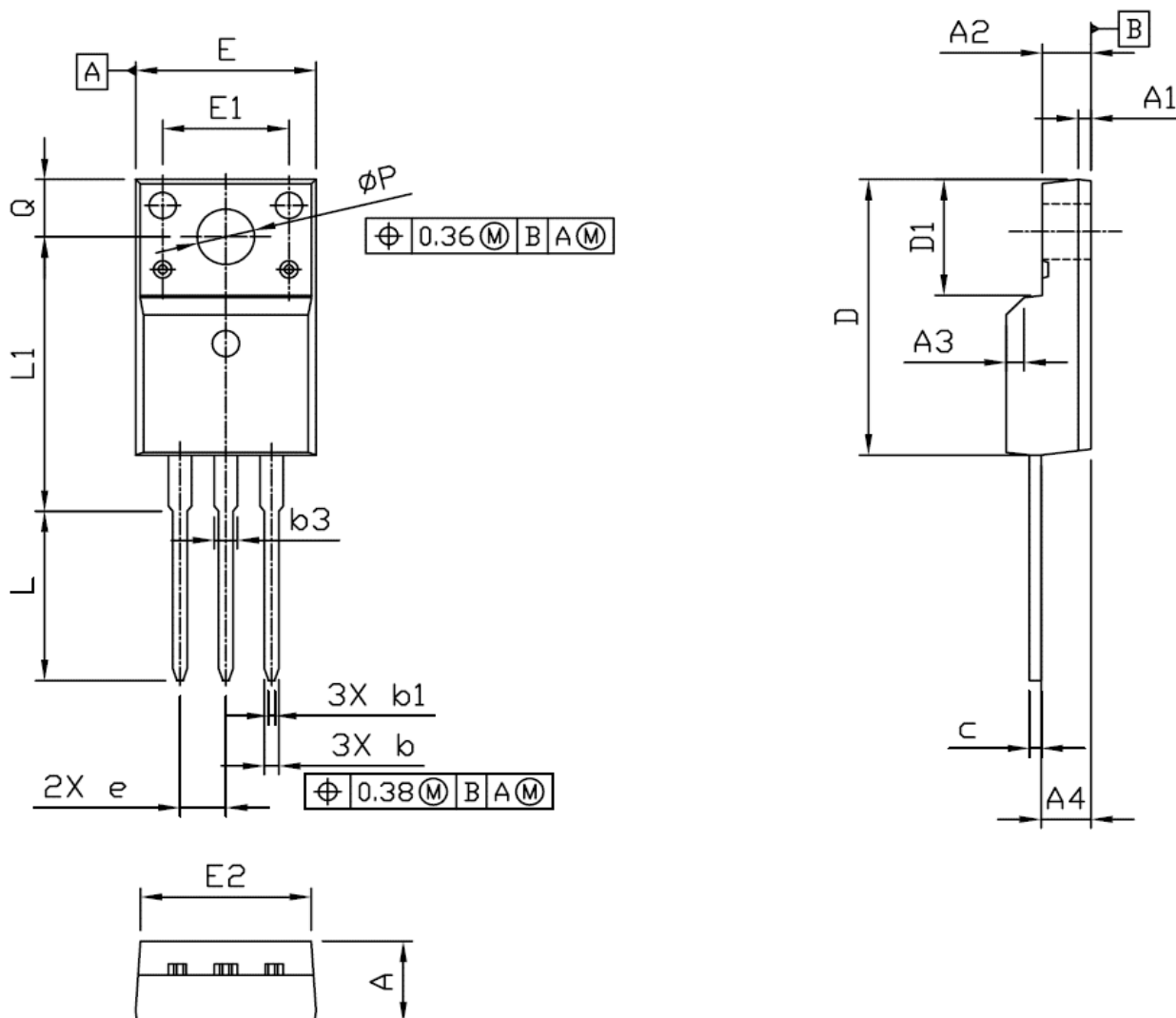


Typical Characteristics



Package Information

TO-220F

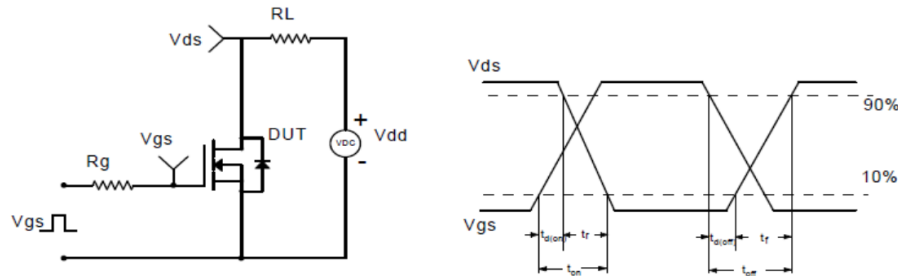


SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	4.50	4.70	4.90	0.177	0.185	0.193	D1	6.48	6.68	6.88	0.255	0.263	0.271
A1	*	0.70	*	*	0.028	*	E	9.96	10.16	10.36	0.392	0.400	0.408
A2	2.34	2.54	2.74	0.092	0.100	0.108	E1	*	7.00	*	*	0.276	*
A3	1X45°			1X45°			E2	9.26	9.46	9.66	0.365	0.372	0.380
A4	2.56	2.76	2.96	0.101	0.109	0.117	e	2.54 BSC			0.10 BSC		
b	0.70	0.80	0.90	0.028	0.031	0.035	L	9.55	9.75	9.95	0.376	0.384	0.392
b1	0.25	0.35	0.45	0.010	0.014	0.018	L1	15.60	15.80	16.00	0.614	0.622	0.630
b3	1.18	1.28	1.47	0.046	0.050	0.058	Q	3.20	3.30	3.40	0.126	0.130	0.134
c	0.45	0.50	0.60	0.018	0.020	0.024	ΦP	3.08	3.18	3.28	0.121	0.125	0.129
D	15.67	15.87	16.07	0.617	0.625	0.633							

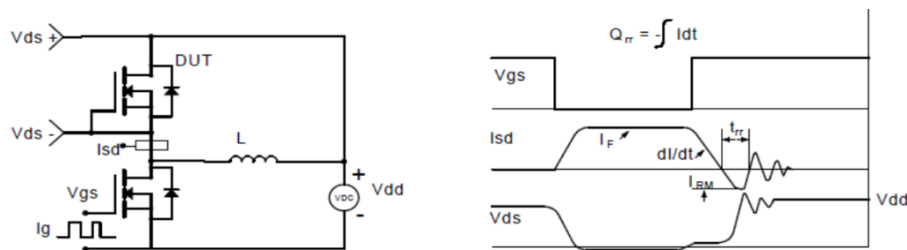
Avalanche Test Circuit and Waveforms



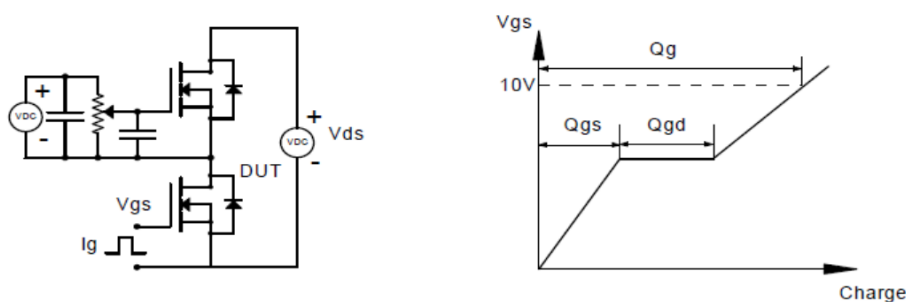
Switching Time Test Circuit and Waveforms



Diode Recovery Test Circuit and Waveforms



Gate Charge Test Circuit and Waveform



Customer Service

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